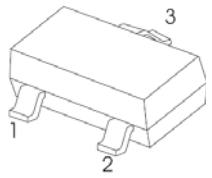
DONGGUAN NANJING ELECTRONICS LTD.,

SOT-23 Plastic-Encapsulate Diodes

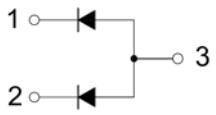
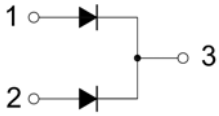
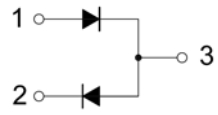
BAV23A/C/S SCHOTTKY BARRIER DIODE

SOT-23



FEATURES

- Fast Switching Speed
- High Conductance
- For General Purpose Switching Applications

BAV23A	BAV23C	BAV23S
		
MARKING: KT7	MARKING: KT6	MARKING:KL31

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	250	V
V_{RWM}	Working Peak Reverse Voltage		
$V_{R(RMS)}$	RMS Reverse Voltage	175	V
I_O	Average Rectified Output Current	400	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current @ t=1μs	9	A
	@ t=100μs	3	A
	@ t=10ms	1.7	A
P_D	Power Dissipation	350	mW
$R_{\Theta JA}$	Thermal Resistance from Junction to Ambient	286	℃/W
T_j	Junction Temperature	125	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	I_R=100μA	250			V
Reverse current	I_R	V_R=250V			0.1	μA
Forward voltage	V_F	I_F=100mA			1	V
		I_F=200mA			1.25	
Total capacitance	C_{tot}	V_R=0V,f=1MHz			5	pF
Reverse recovery time	t_{rr}	I_F= I_R=30mA, I_{rr}=0.1×I_R, R_L=100Ω			50	ns

B,Jul,2012